

74VHC02; 74VHCT02

Quad 2-input NOR gate

Rev. 01 — 13 August 2009

Product data sheet

1. General description

The 74VHC02; 74VHCT02 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard No. 7-A.

The 74VHC02; 74VHCT02 provide a quad 2-input NOR function.

2. Features

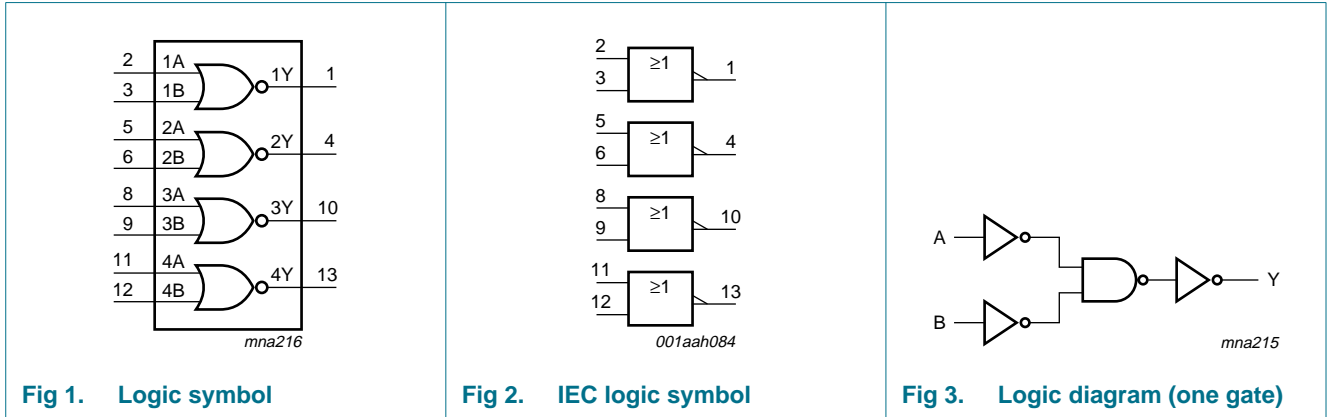
- Balanced propagation delays
- All inputs have a Schmitt-trigger action
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - ◆ The 74VHC02 operates with CMOS input level
 - ◆ The 74VHCT02 operates with TTL input level
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

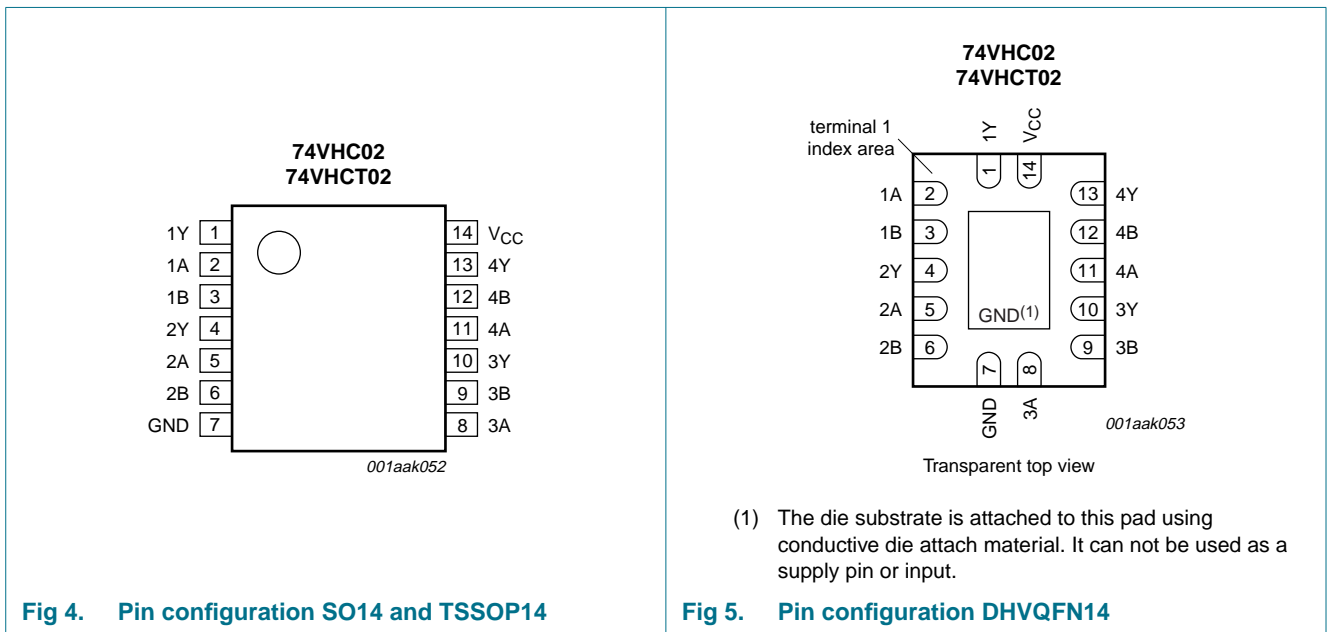
| Type number | Package | | | |
|-------------------------|---|----------|--|----------|
| | Temperature range | Name | Description | Version |
| 74VHC02D 74VHCT02D | $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ | SO14 | plastic small outline package; 14 leads; body width 3.9 mm | SOT108-1 |
| 74VHC02PW 74VHCT02PW | $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ | TSSOP14 | plastic thin shrink small outline package; 14 leads; body width 4.4 mm | SOT402-1 |
| 74VHC02BQ 74VHCT02BQ | $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ | DHVQFN14 | plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm | SOT762-1 |

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

| Symbol | Pin | Description |
|-----------------|-----|----------------|
| 1Y | 1 | data output |
| 1A | 2 | data input |
| 1B | 3 | data input |
| 2Y | 4 | data output |
| 2A | 5 | data input |
| 2B | 6 | data input |
| GND | 7 | ground (0 V) |
| 3A | 8 | data input |
| 3B | 9 | data input |
| 3Y | 10 | data output |
| 4A | 11 | data input |
| 4B | 12 | data input |
| 4Y | 13 | data output |
| V _{CC} | 14 | supply voltage |

6. Functional description

Table 3. Function table^[1]

| Input | | Output |
|-------|----|--------|
| nA | nB | nY |
| L | L | H |
| X | H | L |
| H | X | L |

[1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|-------------------------|--|---------|------|------|
| V_{CC} | supply voltage | | -0.5 | +7.0 | V |
| V_I | input voltage | | -0.5 | +7.0 | V |
| I_{IK} | input clamping current | $V_I < -0.5$ V | [1] -20 | - | mA |
| I_{OK} | output clamping current | $V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V | [1] -20 | +20 | mA |
| I_O | output current | $V_O = -0.5$ V to $(V_{CC} + 0.5$ V) | -25 | +25 | mA |
| I_{CC} | supply current | | - | +75 | mA |
| I_{GND} | ground current | | -75 | - | mA |
| T_{stg} | storage temperature | | -65 | +150 | °C |
| P_{tot} | total power dissipation | $T_{amb} = -40$ °C to +125 °C | [2] - | 500 | mW |

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO14 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.

For TSSOP14 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.

For DHVQFN14 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------|-------------------------------------|---------------------------|-----|-----|----------|------|
| 74VHC02 | | | | | | |
| V_{CC} | supply voltage | | 2.0 | 5.0 | 5.5 | V |
| V_I | input voltage | | 0 | - | 5.5 | V |
| V_O | output voltage | | 0 | - | V_{CC} | V |
| T_{amb} | ambient temperature | | -40 | +25 | +125 | °C |
| $\Delta t/\Delta V$ | input transition rise and fall rate | $V_{CC} = 3.0$ V to 3.6 V | - | - | 100 | ns/V |
| | | $V_{CC} = 4.5$ V to 5.5 V | - | - | 20 | ns/V |
| 74VHCT02 | | | | | | |
| V_{CC} | supply voltage | | 4.5 | 5.0 | 5.5 | V |
| V_I | input voltage | | 0 | - | 5.5 | V |
| V_O | output voltage | | 0 | - | V_{CC} | V |
| T_{amb} | ambient temperature | | -40 | +25 | +125 | °C |
| $\Delta t/\Delta V$ | input transition rise and fall rate | $V_{CC} = 4.5$ V to 5.5 V | - | - | 20 | ns/V |

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|-----------------|---|---|-------|------|------|------------------|------|-------------------|------|------|
| | | | Min | Typ | Max | Min | Max | Min | Max | |
| 74VHC02 | | | | | | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 2.0 V | 1.5 | - | - | 1.5 | - | 1.5 | - | V |
| | | V _{CC} = 3.0 V | 2.1 | - | - | 2.1 | - | 2.1 | - | V |
| | | V _{CC} = 5.5 V | 3.85 | - | - | 3.85 | - | 3.85 | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 2.0 V | - | - | 0.5 | - | 0.5 | - | 0.5 | V |
| | | V _{CC} = 3.0 V | - | - | 0.9 | - | 0.9 | - | 0.9 | V |
| | | V _{CC} = 5.5 V | - | - | 1.65 | - | 1.65 | - | 1.65 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | | | |
| | | I _O = -50 μA; V _{CC} = 2.0 V | 1.9 | 2.0 | - | 1.9 | - | 1.9 | - | V |
| | | I _O = -50 μA; V _{CC} = 3.0 V | 2.9 | 3.0 | - | 2.9 | - | 2.9 | - | V |
| | | I _O = -50 μA; V _{CC} = 4.5 V | 4.4 | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | I _O = -4.0 mA; V _{CC} = 3.0 V | 2.58 | - | - | 2.48 | - | 2.40 | - | V |
| | I _O = -8.0 mA; V _{CC} = 4.5 V | 3.94 | - | - | 3.80 | - | 3.70 | - | V | |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | | | |
| | | I _O = 50 μA; V _{CC} = 2.0 V | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 50 μA; V _{CC} = 3.0 V | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 50 μA; V _{CC} = 4.5 V | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 4.0 mA; V _{CC} = 3.0 V | - | - | 0.36 | - | 0.44 | - | 0.55 | V |
| | I _O = 8.0 mA; V _{CC} = 4.5 V | - | - | 0.36 | - | 0.44 | - | 0.55 | V | |
| I _I | input leakage current | V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V | - | - | 0.1 | - | 1.0 | - | 2.0 | μA |
| I _{CC} | supply current | V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V | - | - | 2.0 | - | 20 | - | 40 | μA |
| C _I | input capacitance | | - | 3 | 10 | - | 10 | - | 10 | pF |

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|------------------|---------------------------|---|-------|-----|------|------------------|------|-------------------|------|------|
| | | | Min | Typ | Max | Min | Max | Min | Max | |
| 74VHCT02 | | | | | | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 4.5 V to 5.5 V | 2.0 | - | - | 2.0 | - | 2.0 | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 4.5 V to 5.5 V | - | - | 0.8 | - | 0.8 | - | 0.8 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V | | | | | | | | |
| | | I _O = -50 µA | 4.4 | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | I _O = -8.0 mA | 3.94 | - | - | 3.80 | - | 3.70 | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V | | | | | | | | |
| | | I _O = 50 µA | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 8.0 mA | - | - | 0.36 | - | 0.44 | - | 0.55 | V |
| I _I | input leakage current | V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V | - | - | 0.1 | - | 1.0 | - | 2.0 | µA |
| I _{CC} | supply current | V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V | - | - | 2.0 | - | 20 | - | 40 | µA |
| ΔI _{CC} | additional supply current | per input pin; V _I = V _{CC} - 2.1 V; other pins at V _{CC} or GND; I _O = 0 A; V _{CC} = 4.5 V to 5.5 V | - | - | 1.35 | - | 1.5 | - | 1.5 | mA |
| C _I | input capacitance | | - | 3 | 10 | - | 10 | - | 10 | pF |

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|-----------------|-------------------------------|---|----------------|--------------------|------|------------------|-----|-------------------|------|------|
| | | | Min | Typ ^[1] | Max | Min | Max | Min | Max | |
| 74VHC02 | | | | | | | | | | |
| t _{pd} | propagation delay | nA, nB to nY; see Figure 6 ^[2] | | | | | | | | |
| | | V _{CC} = 3.0 V to 3.6 V | | | | | | | | |
| | | C _L = 15 pF | - | 3.9 | 7.9 | 1.0 | 9.5 | 1.0 | 10.0 | ns |
| | | C _L = 50 pF | - | 5.5 | 11.4 | 1.0 | 13 | 1.0 | 14.5 | ns |
| | | V _{CC} = 4.5 V to 5.5 V | | | | | | | | |
| | | C _L = 15 pF | - | 2.9 | 5.5 | 1.0 | 6.5 | 1.0 | 7.0 | ns |
| | | C _L = 50 pF | | 4.2 | 7.5 | 1.0 | 8.5 | 1.0 | 9.5 | ns |
| C _{PD} | power dissipation capacitance | C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC} | ^[3] | - | 7.0 | - | - | - | - | pF |

Table 7. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|--|-------------------------------|--|-------|--------------------|-----|------------------|-----|-------------------|-----|------|
| | | | Min | Typ ^[1] | Max | Min | Max | Min | Max | |
| 74VHCT02; V_{CC} = 4.5 V to 5.5 V | | | | | | | | | | |
| t _{pd} | propagation delay | nA, nB to nY; see Figure 6 ^[2] | | | | | | | | |
| | | C _L = 15 pF | - | 3.8 | 5.5 | 1.0 | 6.5 | 1.0 | 7.0 | ns |
| | | C _L = 50 pF | - | 5.1 | 7.5 | 1.0 | 8.5 | 1.0 | 9.5 | ns |
| C _{PD} | power dissipation capacitance | C _L = 50 pF; f _i = 1 MHz; V _i = GND to V _{CC} ^[3] | - | 8.0 | - | - | - | - | - | pF |

- [1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

11. Waveforms

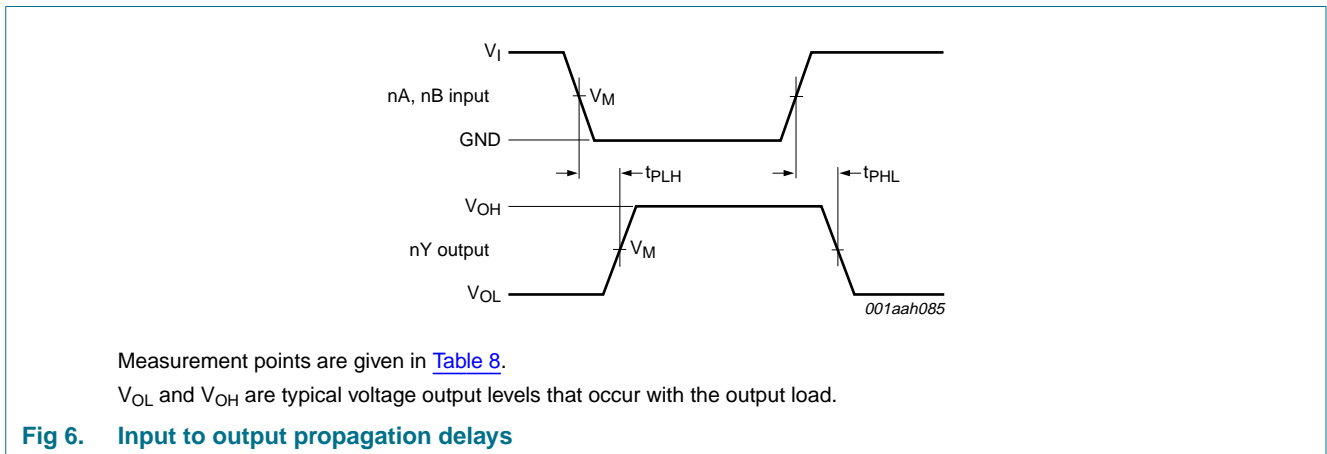
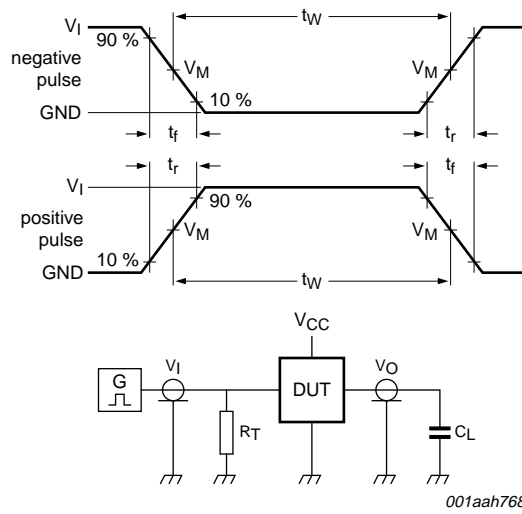


Table 8. Measurement points

| Type | Input | Output |
|----------|--------------------|--------------------|
| | V _M | V _M |
| 74VHC02 | 0.5V _{CC} | 0.5V _{CC} |
| 74VHCT02 | 1.5 V | 0.5V _{CC} |



001aah768

Test data is given in [Table 9](#).

Definitions test circuit:

R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = load capacitance including jig and probe capacitance.

Fig 7. Load circuitry for measuring switching times

Table 9. Test data

| Type | Input | | Load | Test |
|----------|----------|---------------|--------------|--------------------|
| | V_I | t_r, t_f | C_L | |
| 74VHC02 | V_{CC} | ≤ 3.0 ns | 15 pF, 50 pF | t_{PLH}, t_{PHL} |
| 74VHCT02 | 3.0 V | ≤ 3.0 ns | 15 pF, 50 pF | t_{PLH}, t_{PHL} |

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

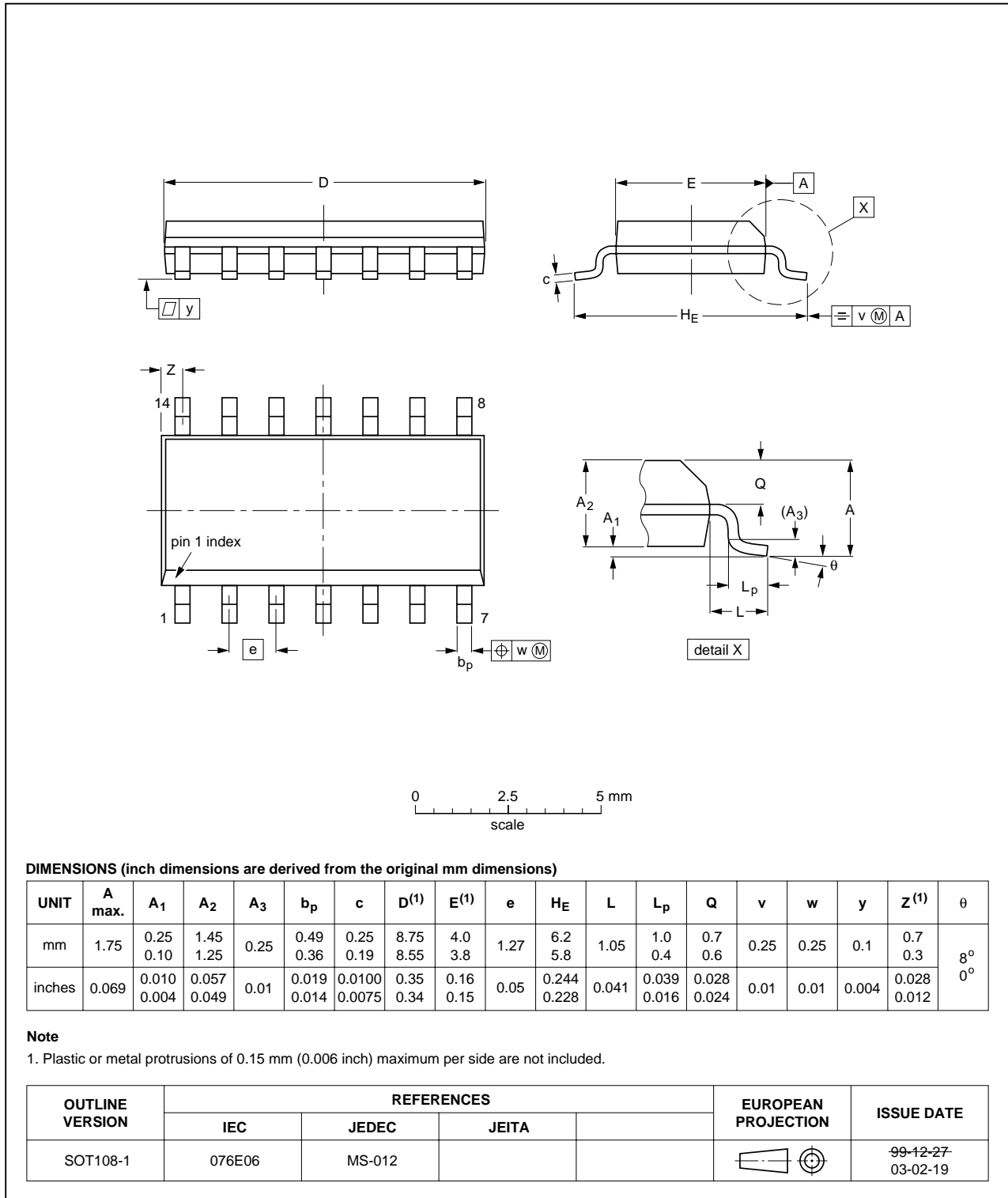


Fig 8. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

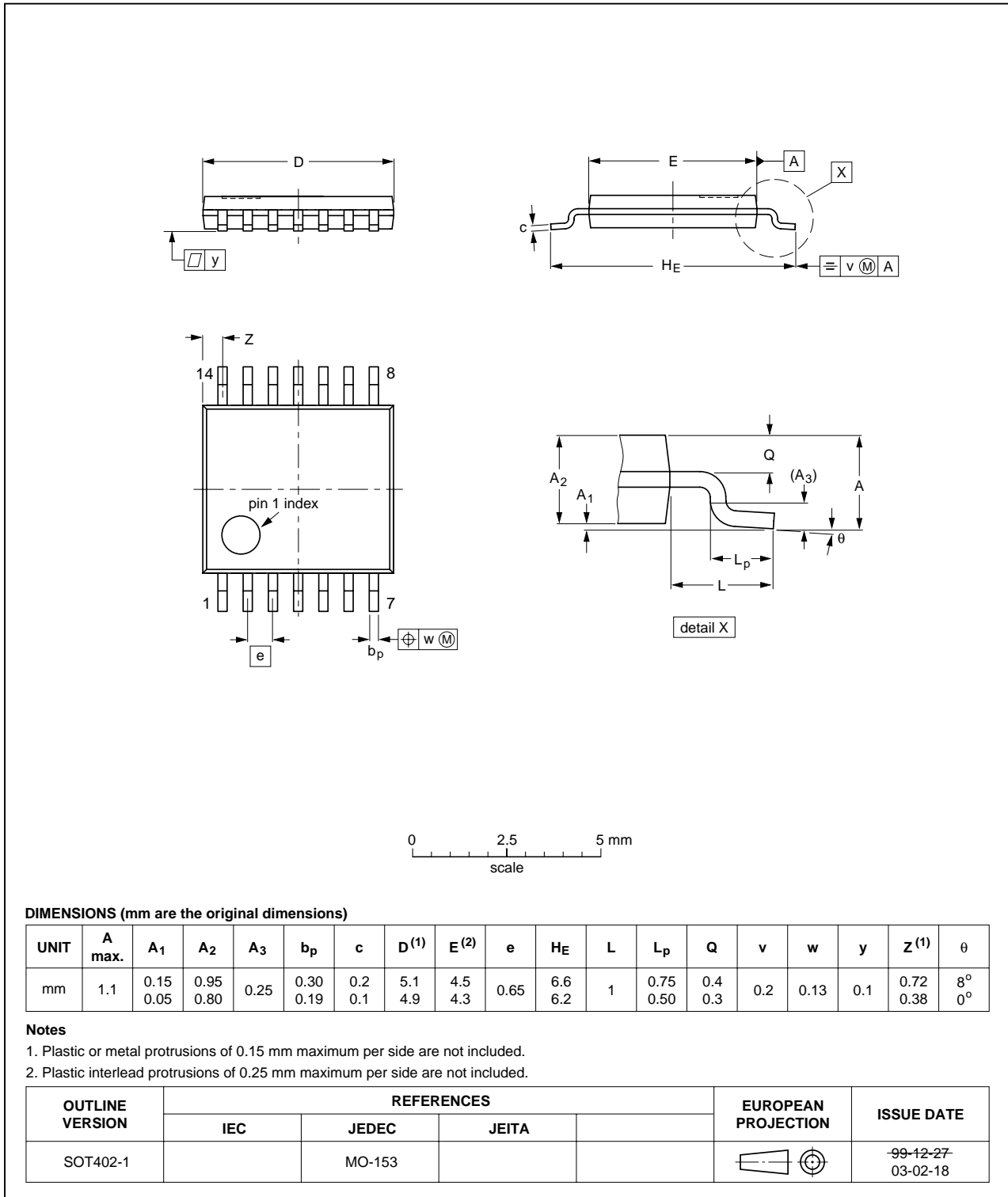


Fig 9. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

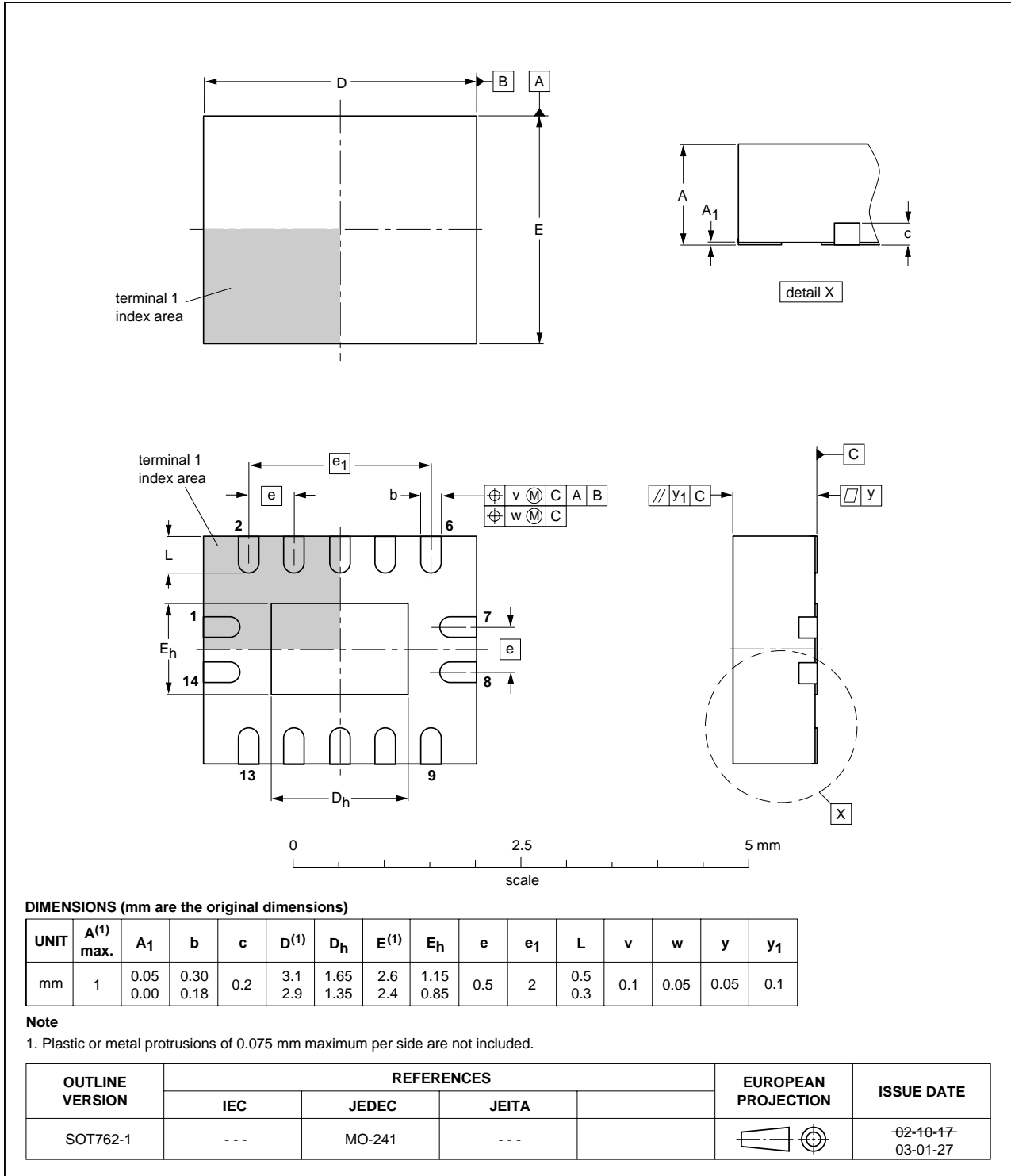


Fig 10. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

| Acronym | Description |
|---------|--|
| CDM | Charged Device Model |
| CMOS | Complementary Metal-Oxide Semiconductor |
| DUT | Device Under Test |
| ESD | ElectroStatic Discharge |
| HBM | Human Body Model |
| LSTTL | Low-power Schottky Transistor-Transistor Logic |
| MM | Machine Model |

14. Revision history

Table 11. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| 74VHC_VHCT02_1 | 20090813 | Product data sheet | - | - |

15. Legal information

15.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
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